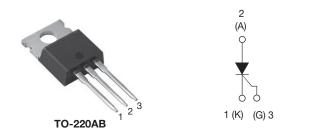


Vishay Semiconductors

FREE

# Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS		
I <sub>T(AV)</sub>	16 A	
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V	
V <sub>TM</sub>	1.25 V	
I <sub>GT</sub>	45 mA	
TJ	-40 °C to 125 °C	
Package	TO-220AB	
Circuit configuration	Single SCR	

### FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see COMPLIANT www.vishay.com/doc?99912
   HALOGEN

### **APPLICATIONS**

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

### DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS				
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS				
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	18	22	A	

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
I <sub>T(AV)</sub>	Sinusoidal waveform	16	А	
I <sub>RMS</sub>		25	A	
V <sub>RRM</sub> /V <sub>DRM</sub>		800/1200	V	
I <sub>TSM</sub>		320	A	
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V	
dV/dt		500	V/µs	
dl/dt		150	A/µs	
TJ		-40 to 125	°C	

VOLTAGE RATINGS					
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 ℃ mA		
VS-25TTS08PbF, VS-25TTS08-M3	800	800	10		
VS-25TTS12PbF, VS-25TTS12-M3	1200	1200	10		

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VS-25TTS..PbF Series, VS-25TTS..-M3 Series

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ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL	TEST CO	VAL	UNITS		
PARAMEIER	SYMBOL TEST CONDITIONS		NDITION5	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{\rm C} = 93 ^{\circ}{\rm C},  180^{\circ}  {\rm conduct}$	tion half sine wave	1	6	
Maximum RMS on-state current	I <sub>RMS</sub>			2	25	А
Maximum peak, one-cycle,	1	10 ms sine pulse, rated V	√ <sub>RRM</sub> applied	2	70	~
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volt	age reapplied	3	20	
Maximum 12t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated	/ <sub>RRM</sub> applied	3	65	A2-
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no volt	515		A <sup>2</sup> s	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10 ms, no volta	ge reapplied	51	52	A²√s
Maximum on-state voltage drop	V <sub>TM</sub>	16 A, T <sub>J</sub> = 25 °C		1.	25	V
On-state slope resistance	rt 12.0				2.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		1.0		V
		T <sub>J</sub> = 25 °C		0	.5	
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		
Holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T = 1 A$ , $T_J = 25 \ ^{\circ}C$		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear to 80 °C, $V_{DRM} = R_g - k = Open$		50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	А	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, $T_J = -10 \text{ °C}$	2.5		
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	2.0		
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Deted value	0.25		
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T 105 %C	4	μs
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110	

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### **Vishay Semiconductors**

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to 125	°C
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque –	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf ⋅ in)
Marking device			Coop atula TO 220AB	25TTS08	
			Case style TO-220AB	25T	FS12

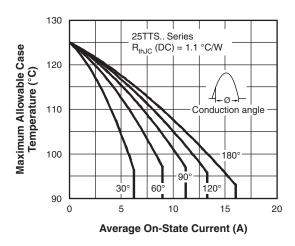


Fig. 1 - Current Rating Characteristics

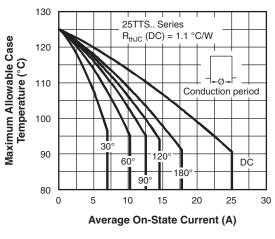


Fig. 2 - Current Rating Characteristics

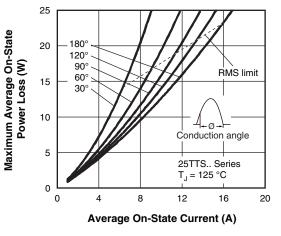


Fig. 3 - On-State Power Loss Characteristics

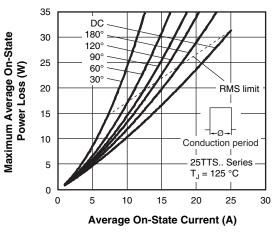


Fig. 4 - On-State Power Loss Characteristics

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## VS-25TTS..PbF Series, VS-25TTS..-M3 Series

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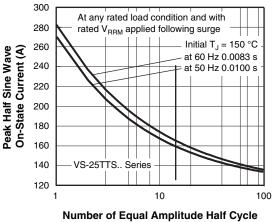
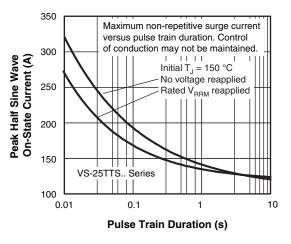




Fig. 5 - Maximum Non-Repetitive Surge Current





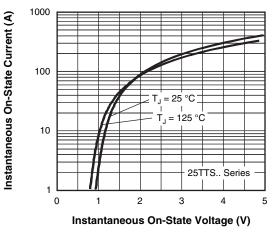


Fig. 7 - On-State Voltage Drop Characteristics

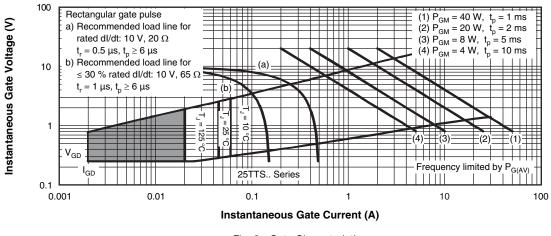


Fig. 8 - Gate Characteristics

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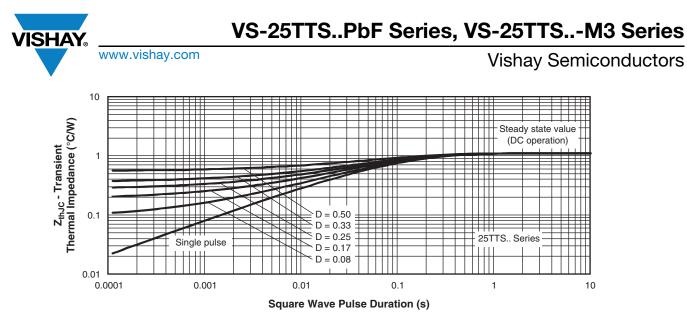


Fig. 9 - Thermal Impedance ZthJC Characteristics

### **ORDERING INFORMATION TABLE**

Device code	VS-	25	т	т	s	12	PbF	
		(2)	(3)	(4)	(5)	(6)	(7)	
	$\bigcirc$		J	$\bigcirc$	J	J	$\cdot$	
	1	- Visł	nay Sem	niconduc	ctors pro	duct		
	2	- Cur	rent rati	ng (25 =	25 A)			
	3 .	- Circ	uit conf	iguratior	n:			
		Т =	Single t	hyristor				
	4	- Pac	kage:					
		T =	TO-220	AB				
	5 -	. Тур	e of silio	con:				
		S =	Standa	rd recov	ery recti	fier		
	6 -	- Volt	age rati	ng —				3 = 800 V = 1200 V
	7	- Envi	ronmen	tal digit:			12	.200 1
		PbF	= Lead	(Pb)-fre	e and R	oHS co	mpliant	
							-	terminations lead (Pb)-

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-25TTS08PbF	50	1000	Antistatic plastic tubes		
VS-25TTS08-M3	50	1000	Antistatic plastic tubes		
VS-25TTS12PbF	50	1000	Antistatic plastic tubes		
VS-25TTS12-M3	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS			
Dimensions		www.vishay.com/doc?95222	
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225	
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028	

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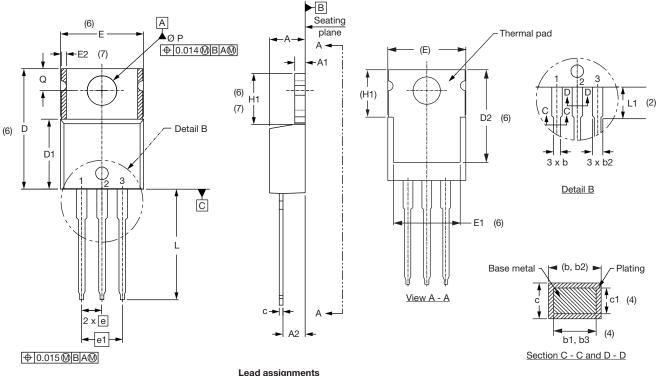
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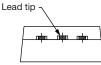


**Vishay Semiconductors** 

**TO-220AB** 

#### **DIMENSIONS** in millimeters and inches





.ead	assignments

**Diodes** 

3. - Anode

1. - Anode/open 2. - Cathode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- <sup>(3)</sup> Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed  $0.127 \text{ mm} (0.005^{\circ})$  per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left( 4\right) }$  Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		
0	90 1	0 93	90 1	0 93	

Conforms to JEDEC outline TO-220AB

- $^{(7)}$  Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- Outline conforms to JEDEC TO-220, except A2 (maximum) and (8) D2 (minimum) where dimensions are derived from the actual package outline

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